TOSHIBA Infrared LED GaAs Infrared Emitter

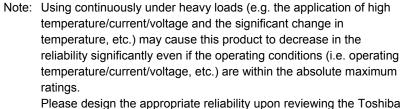
# TLN108(F)

Lead(Pb)-Free Opto-Electronic Switches Tape And Card Readers Equipment Using Infrared Transmission

- TO-18 metal package
- High radiant intensity:  $I_E = 20 \text{ mW/sr}$  (typ.)
- Excellent radiant-intensity linearity. Modulation by pulse operation and high frequency is possible.
- Highly reliable due to hermetic seal

Characteristic	Symbol	Rating	Unit
Forward current	١ <sub>F</sub>	100	mA
Forward current derating (Ta > 25°C)	ΔI <sub>F</sub> / °C	-1	mA / °C
Pulse forward current (Note 1)	I <sub>FP</sub>	1	А
Reverse voltage	V <sub>R</sub>	5	V
Operating temperature range	T <sub>opr</sub>	-40~125	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

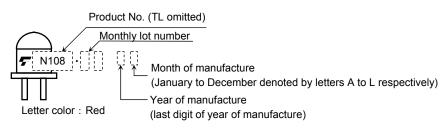
## Absolute Maximum Ratings (Ta = 25°C)

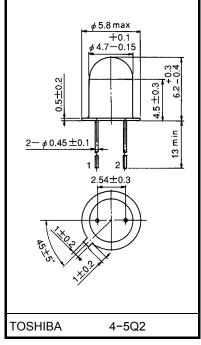


Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width  $\leq 100 \mu s$ , repetitive frequency = 100 Hz

# Markings





#### Weight: 0.33 g (typ.)

### **Pin Connection**

#### 1 • • • 2

- 1. Anode
- 2. Cathode (case)

Unit: mm

# **Optical And Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Forward voltage	VF	I <sub>F</sub> = 50 mA	_	1.3	1.4	V
Pulse forward voltage	V <sub>FP</sub>	I <sub>FP</sub> = 1 A	_	2.4	_	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 5 V	_	_	10	μA
Radiant intensity	١ <sub>E</sub>	I <sub>F</sub> = 50 mA	10	20	_	mW / sr
Radiant power	Po	I <sub>F</sub> = 50 mA	_	3	_	mW
Capacitance	CT	V <sub>R</sub> = 0, f = 1 MHz	_	30	_	pF
Peak emission wavelength	λ <sub>P</sub>	I <sub>F</sub> = 50 mA	_	940	_	nm
Spectral line half width	Δλ	I <sub>F</sub> = 50 mA	_	50	—	nm
Half value angle	$\theta \frac{1}{2}$	I <sub>F</sub> = 50 mA	—	±8	—	0

# Precautions

Please be careful of the followings.

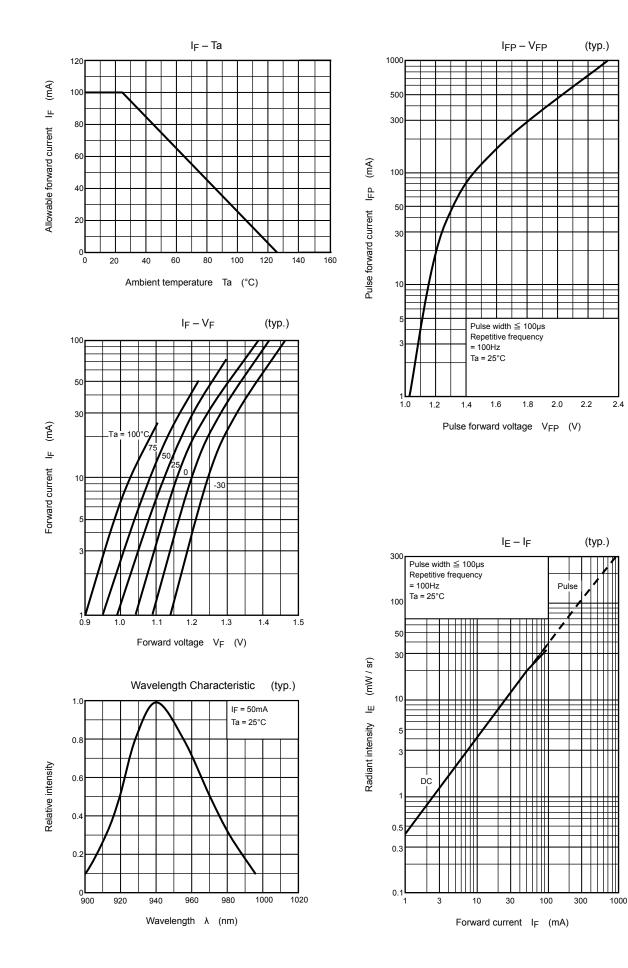
1. Soldering temperature: 260°C max Soldering time: 5s max

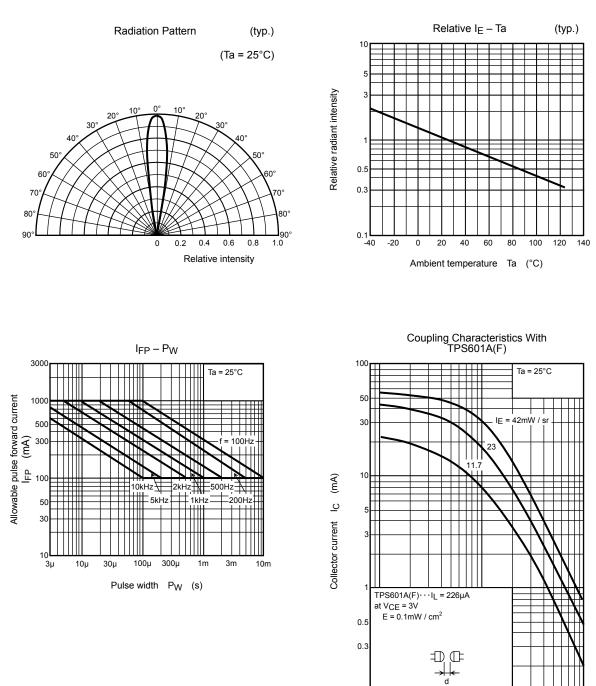
(Soldering must be performed 1.5m from the bottom of the package.)

- 2. When forming the leads, bend each lead under the 2mm from the body of the device. Soldering must be performed after the leads have been formed.
- 3. Radiant intensity falls over time due to the current which flows in the infrared LED. When designing a circuit, take into account this change in radiant power over time. The ratio of fluctuation in radiation intensity to fluctuation in optical output is 1 : 1.

$$\frac{I_{\rm E}(t)}{I_{\rm E}(0)} = \frac{P_{\rm O}(t)}{P_{\rm O}(0)}$$

# **TOSHIBA**





0.1

1

10

Distance d (mm)

5

3

30 50

100

# **RESTRICTIONS ON PRODUCT USE**

20070701-EN

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- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
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